

# HN1B01FDW1T1

## Complementary Dual General Purpose Amplifier Transistor

### PNP and NPN Surface Mount

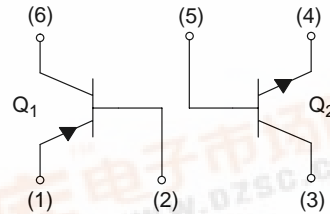


ON Semiconductor®

<http://onsemi.com>

#### Features

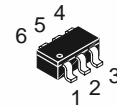
- High Voltage and High Current:  $V_{CEO} = 50\text{ V}$ ,  $I_C = 200\text{ mA}$
- High  $h_{FE}$ :  $h_{FE} = 200 \sim 400$
- Moisture Sensitivity Level: 1
- ESD Rating
  - Human Body Model: 3A
  - Machine Model: C
- Pb-Free Package is Available



#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current – Continuous	$I_C$	200	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

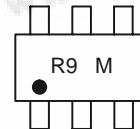


SC-74  
CASE 318F  
STYLE 3

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	$P_D$	380	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

#### MARKING DIAGRAM



R9 = Device Code  
M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
HN1B01FDW1T1	SC-74	3000/Tape & Reel
HN1B01FDW1T1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## Q1: PNP

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage ( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-50	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-60	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-7.0	-	Vdc
Collector–Base Cutoff Current ( $V_{CB} = 45\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-0.1	$\mu\text{A}$
Collector–Emitter Cutoff Current ( $V_{CE} = 10\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ , $T_A = 80^\circ\text{C}$ )	$I_{CEO}$	- - -	-0.1 -2.0 -1.0	$\mu\text{A}$ $\mu\text{A}$ mA
DC Current Gain (Note 1) ( $V_{CE} = 6.0\text{ Vdc}$ , $I_C = 2.0\text{ mA}$ )	$h_{FE}$	-200	-400	-
Collector–Emitter Saturation Voltage ( $I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$ )	$V_{CE(sat)}$	-0.15	-0.3	Vdc

## Q2: NPN

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage ( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	50	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	60	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	7.0	-	Vdc
Collector–Base Cutoff Current ( $V_{CB} = 45\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	0.1	$\mu\text{A}$
Collector–Emitter Cutoff Current ( $V_{CE} = 10\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ , $T_A = 80^\circ\text{C}$ )	$I_{CEO}$	- - -	0.1 2.0 1.0	$\mu\text{A}$ $\mu\text{A}$ mA
DC Current Gain (Note 1) ( $V_{CE} = 6.0\text{ Vdc}$ , $I_C = 2.0\text{ mA}$ )	$h_{FE}$	200	400	-
Collector–Emitter Saturation Voltage ( $I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$ )	$V_{CE(sat)}$	0.15	0.25	Vdc

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , D.C.  $\leq 2\%$ .

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## Typical Electrical Characteristics: PNP Transistor

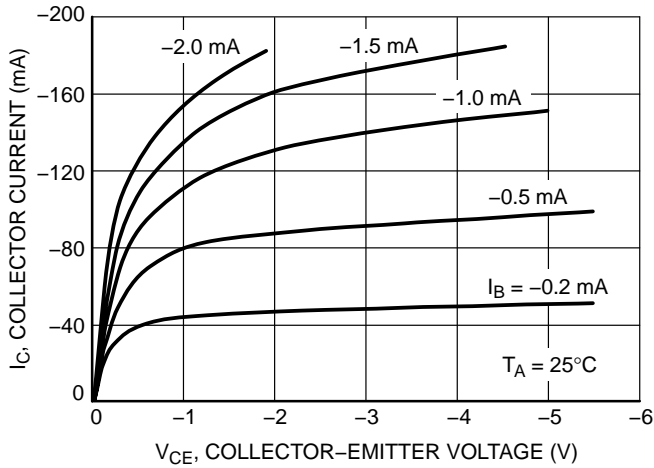


Figure 1. Collector Saturation Region

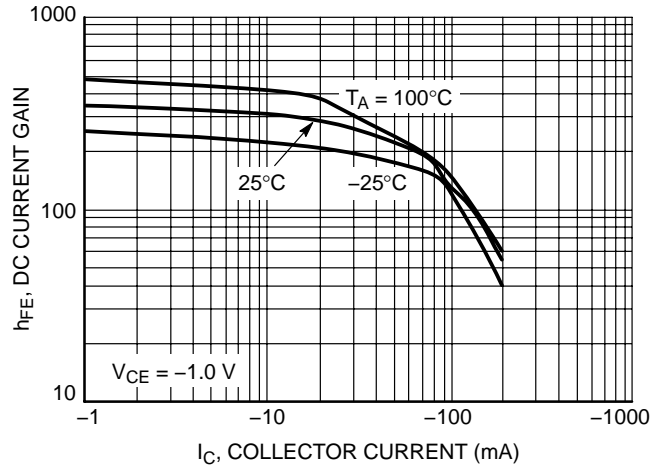


Figure 2. DC Current Gain

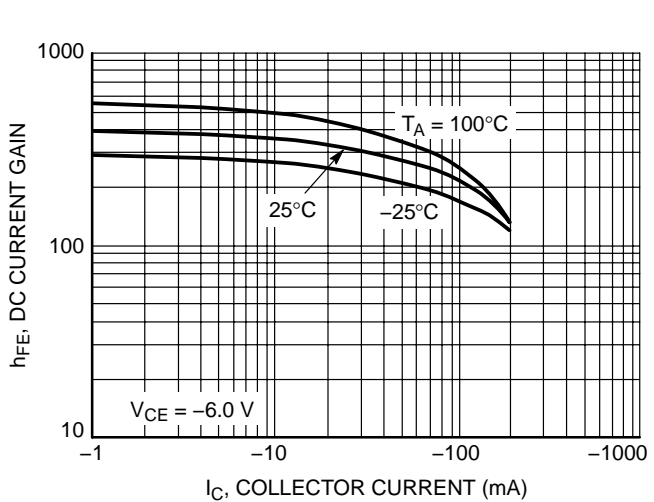


Figure 3. DC Current Gain

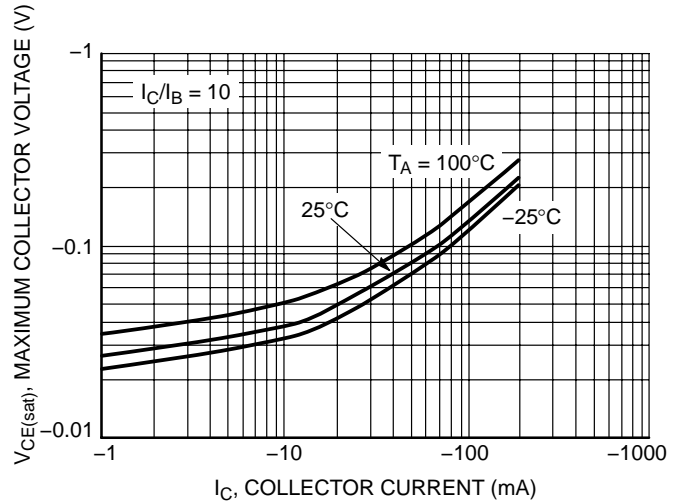


Figure 4.  $V_{CE(sat)}$  versus  $I_C$

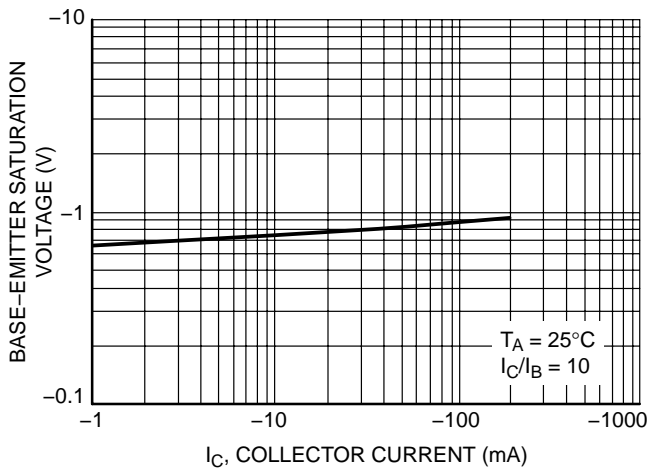


Figure 5.  $V_{BE(sat)}$  versus  $I_C$

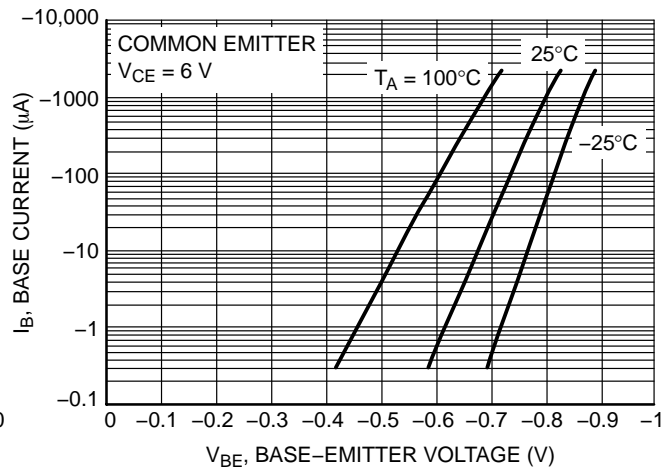


Figure 6. Base-Emitter Voltage

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## Typical Electrical Characteristics: NPN Transistor

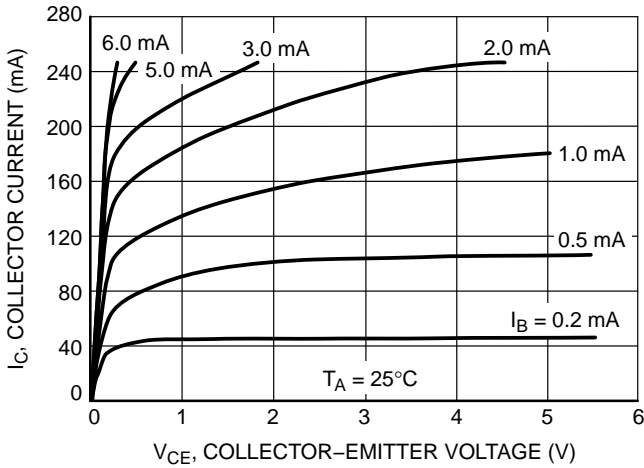


Figure 7. Collector Saturation Voltage

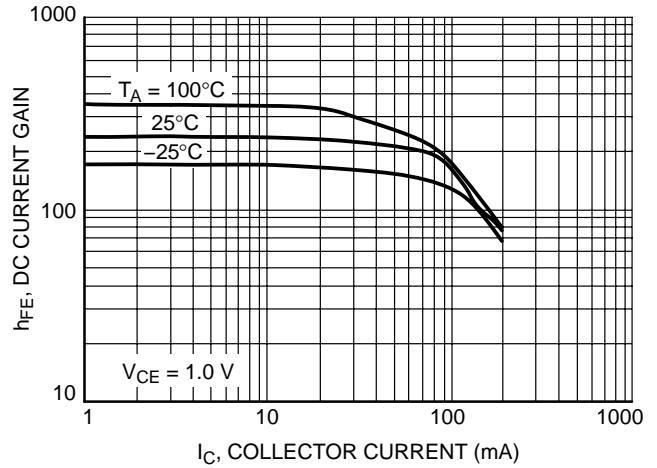


Figure 8. DC Current Gain

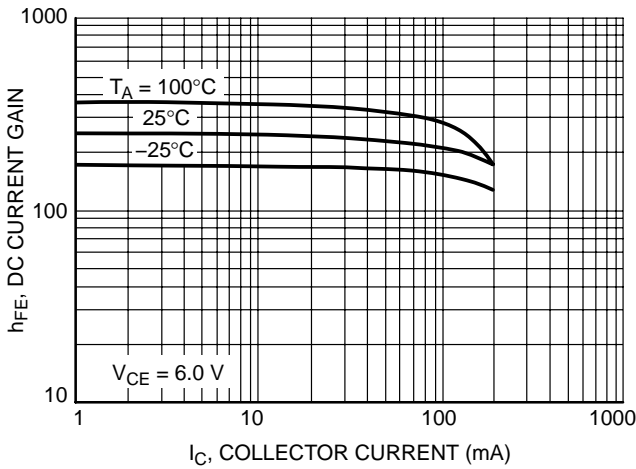


Figure 9. DC Current Gain

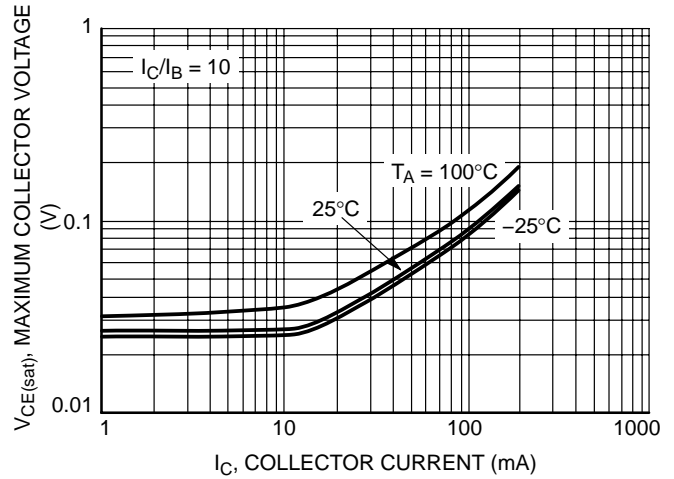


Figure 10.  $V_{CE(sat)}$  versus  $I_C$

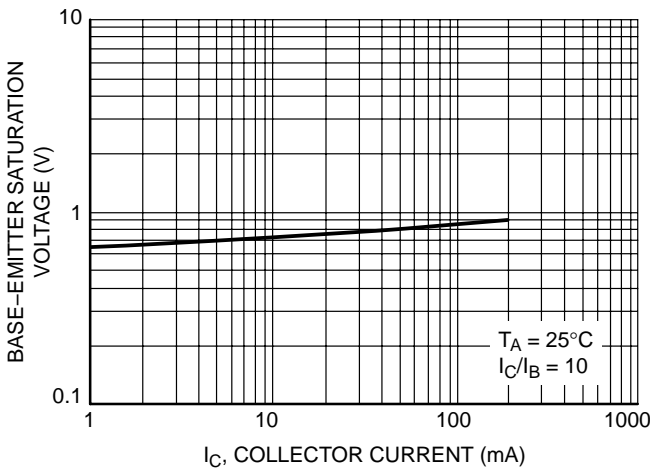


Figure 11.  $V_{BE(sat)}$  versus  $I_C$

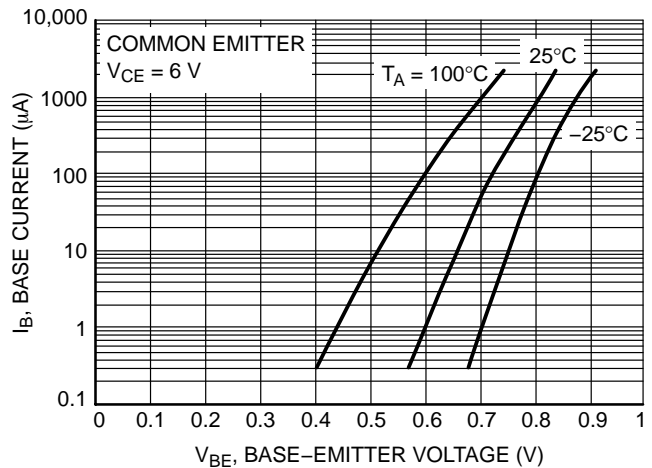
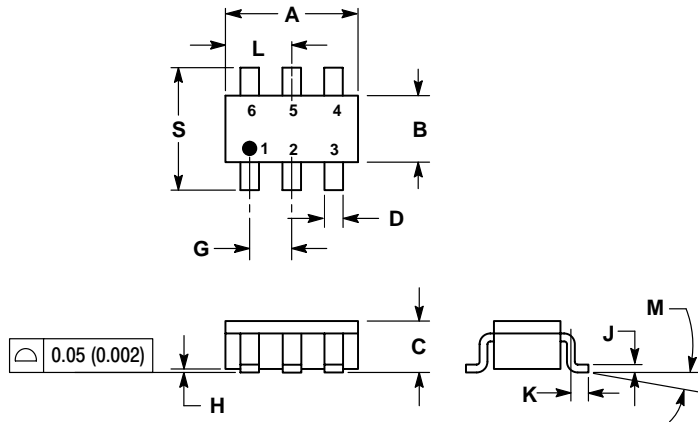


Figure 12. Base-Emitter Voltage

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## PACKAGE DIMENSIONS

SC-74  
CASE 318F-05  
ISSUE K

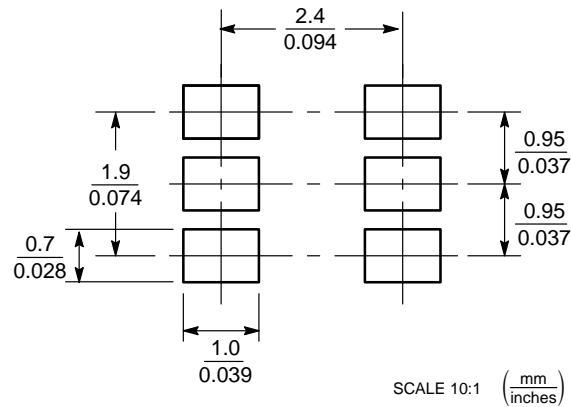


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318F-01, -02, -03 OBSOLETE. NEW STANDARD 318F-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1142	0.1220	2.90	3.10
B	0.0512	0.0669	1.30	1.70
C	0.0354	0.0433	0.90	1.10
D	0.0098	0.0197	0.25	0.50
G	0.0335	0.0413	0.85	1.05
H	0.0005	0.0040	0.013	0.100
J	0.0040	0.0102	0.10	0.26
K	0.0079	0.0236	0.20	0.60
L	0.0493	0.0649	1.25	1.65
M	0°	10°	0°	10°
S	0.0985	0.1181	2.50	3.00


- STYLE 3:  
PIN 1. EMITTER 1  
2. BASE 1  
3. COLLECTOR 2  
4. EMITTER 2  
5. BASE 2  
6. COLLECTOR 1

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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